



SEMITOP® 2

IGBT module

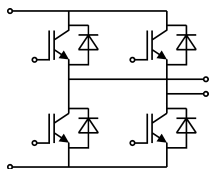
SK 15 GH 066

Features*

- Compact design
- One screw mounting module
- Heat transfer and insulation through direct copper bonded aluminium oxide ceramic (DBC)
- 600V Trench IGBT3 technology
- 600V CAL IHD diode technology
- Integrated NTC temperature sensor
- UL recognized, file no. E 63 532

Typical Applications

- DC/DC Converter
- Motor Drives
- Welding



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Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V _{CES}	T _j = 25 °C		600	V
I _C	T _j = 175 °C	T _s = 25 °C	24	A
		T _s = 70 °C	20	A
I _{Cnom}			15	A
I _{CRM}			30	A
V _{GES}			-20 ... 20	V
t _{psc}	V _{CC} = 360 V V _{GE} ≤ 15 V V _{CES} ≤ 600 V	T _j = 150 °C	6	μs
T _j			-40 ... 175	°C
Inverse - Diode				
V _{RRM}	T _j = 25 °C		600	V
I _F	T _j = 175 °C	T _s = 25 °C	32	A
		T _s = 70 °C	25	A
I _{FRM}			30	A
I _{FSM}	10 ms, sin 180°, T _j = 150 °C		95	A
T _j			-40 ... 175	°C
Module				
I _{t(RMS)}	ΔT _{terminal} at PCB joint = 30 K, per pin		60	A
T _{stg}			-40 ... 125	°C
V _{isol}	AC, sinusoidal, t = 1 min		2500	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Inverter - IGBT						
V _{CE(sat)}	I _C = 15 A	T _J = 25 °C		1.45	1.90	V
	V _{GE} = 15 V chiplevel	T _J = 150 °C		1.65	2.05	V
V _{CE0}	chiplevel	T _J = 25 °C		0.90	1.00	V
		T _J = 150 °C		0.85	0.90	V
r _{CE}	V _{GE} = 15 V	T _J = 25 °C		37	60	mΩ
	chiplevel	T _J = 150 °C		53	77	mΩ
V _{GE(th)}	V _{GE} = V _{CE} , I _C = 0.21 mA		5	5.8	6.5	V
I _{CES}	V _{GE} = 0 V, V _{CE} = 600 V, T _J = 25 °C				0.1	mA
C _{ies}	V _{CE} = 25 V V _{GE} = 0 V	f = 1 MHz		0.86		nF
C _{oes}		f = 1 MHz		0.055		nF
C _{res}		f = 1 MHz		0.024		nF
Q _G	V _{GE} = -8V ... +15V			100		nC
R _{Gint}	T _J = 25 °C			0		Ω
t _{d(on)}	V _{CC} = 300 V	T _J = 150 °C		9		ns
t _r	I _C = 15 A	T _J = 150 °C		9		ns
E _{on}	R _{G on} = 6.2 Ω	T _J = 150 °C		0.3		mJ
	R _{G off} = 6.2 Ω	T _J = 150 °C		135		ns
t _{d(off)}	di/dt _{on} = 1506 A/μs	T _J = 150 °C		68		ns
t _f	di/dt _{off} = 325 A/μs	T _J = 150 °C		0.35		mJ
E _{off}	V _{GE} = +15/-8 V	T _J = 150 °C		2.19		K/W
R _{th(j-s)}	per IGBT, λ _{paste} =0.8 W/(mK)					

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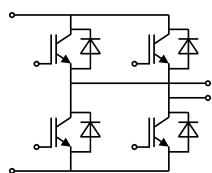
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Characteristics

Symbol	Conditions		min.	typ.	max.	Unit
Inverse - Diode						
$V_F = V_{EC}$	$I_F = 15\text{ A}$	$T_j = 25\text{ °C}$		1.23	1.48	V
	chipelevel	$T_j = 150\text{ °C}$		1.15	1.34	V
V_{F0}	chipelevel	$T_j = 25\text{ °C}$		0.99	1.10	V
		$T_j = 150\text{ °C}$		0.80	0.89	V
r_F	chipelevel	$T_j = 25\text{ °C}$		16	26	mΩ
		$T_j = 150\text{ °C}$		23	30	mΩ
I_{RRM}	$I_F = 15\text{ A}$	$T_j = 150\text{ °C}$		16		A
Q_{rr}	$di/dt_{off} = 1506\text{ A/μs}$	$T_j = 150\text{ °C}$		1.25		μC
E_{rr}	$V_{GE} = -8\text{ V}$	$T_j = 150\text{ °C}$		0.26		mJ
	$V_{CC} = 300\text{ V}$					
$R_{th(j-s)}$	per Diode, $\lambda_{paste}=0.8\text{ W/(mK)}$			2.7		K/W
Module						
L_{CE}				-		nH
M_s	to heatsink		1.8		2	Nm
w				19		g



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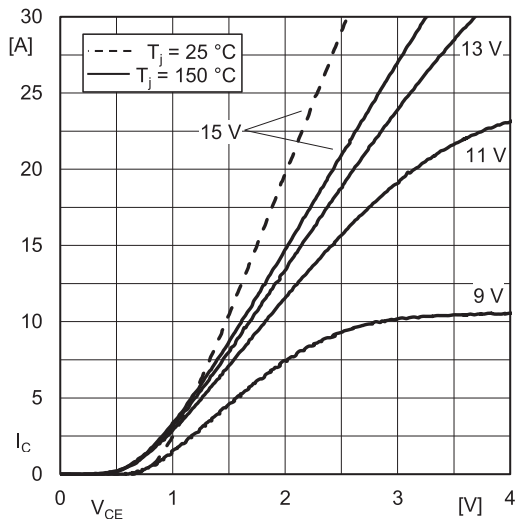


Fig. 1: Typ. IGBT output characteristic, incl. $R_{CC+EE'}$

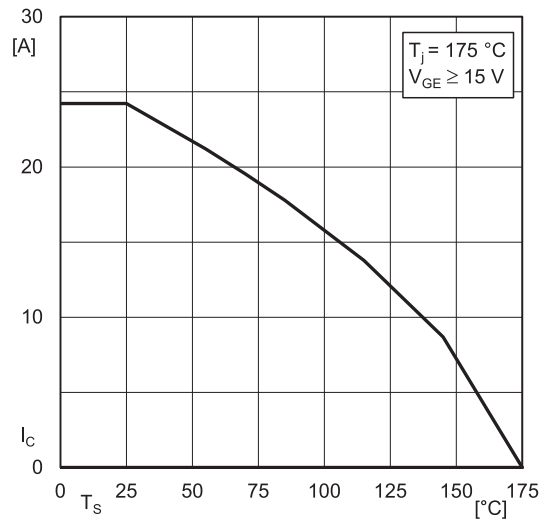


Fig. 2: Rated current vs. temperature $I_C = f(T_S)$

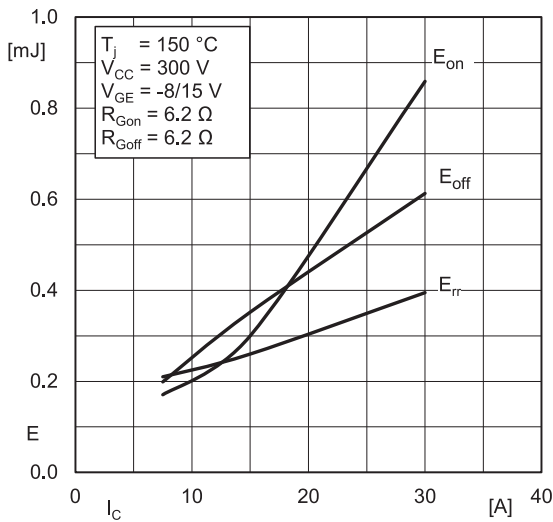


Fig. 3: Typ. turn-on /-off energy = $f(I_C)$

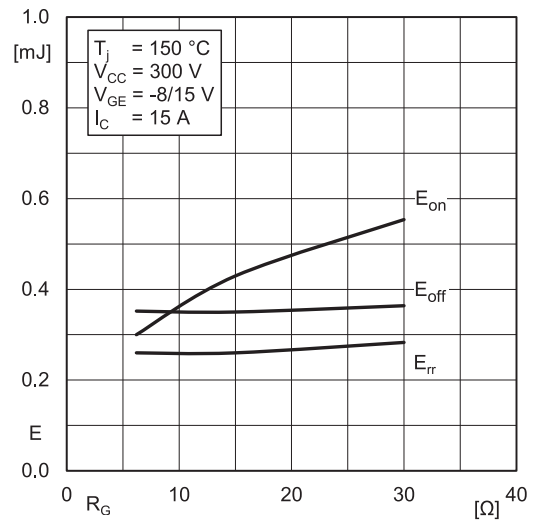


Fig. 4: Typ. turn-on /-off energy = $f(R_G)$

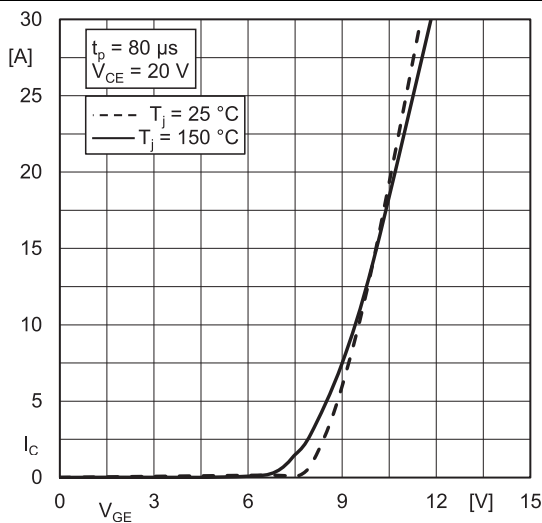


Fig. 5: Typ. IGBT transfer characteristic

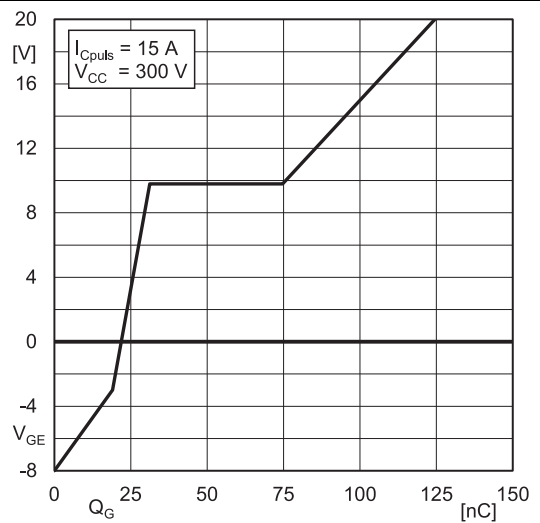


Fig. 6: Typ. IGBT gate charge characteristic

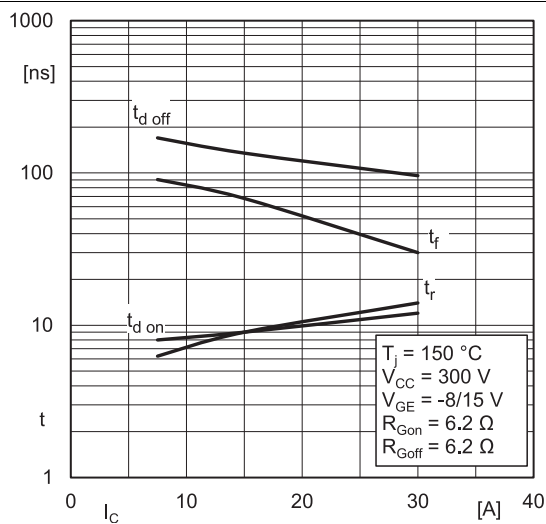


Fig. 7: Typ. switching times = $f(I_C)$

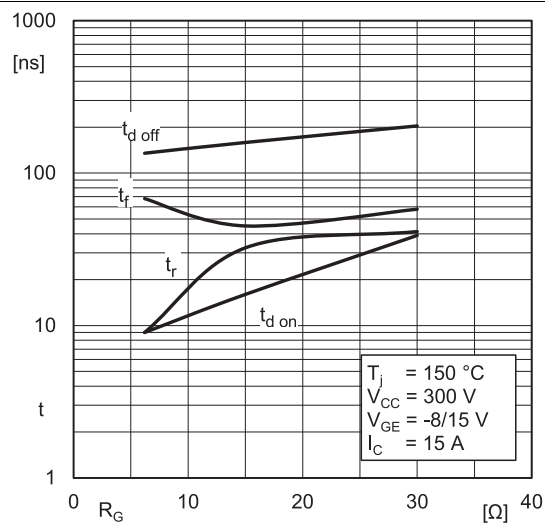


Fig. 8: Typ. switching times = $f(R_G)$

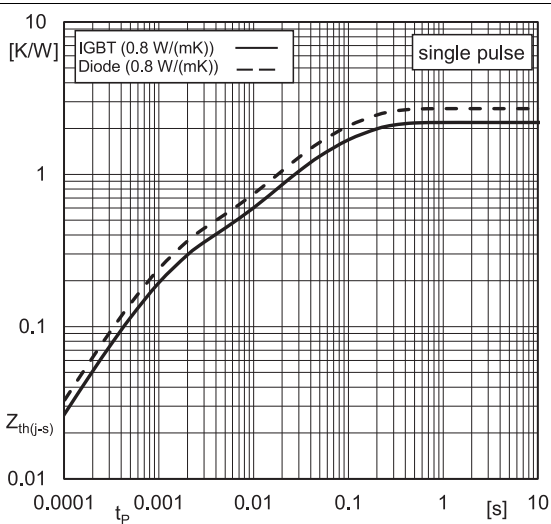


Fig. 9: Typ. transient thermal impedance

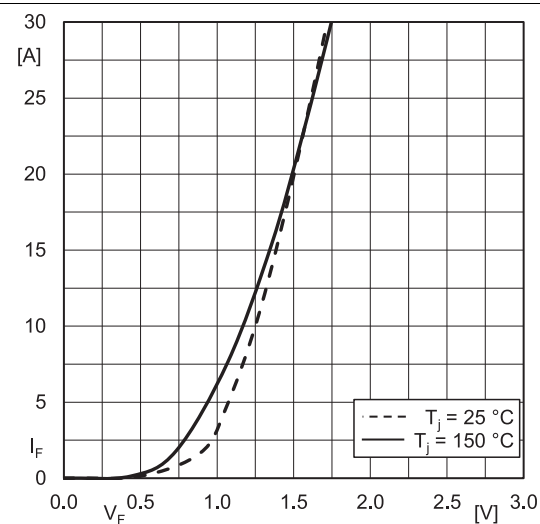


Fig. 10: Typ. Diode forward charact., incl. $R_{CC'} + EE'$

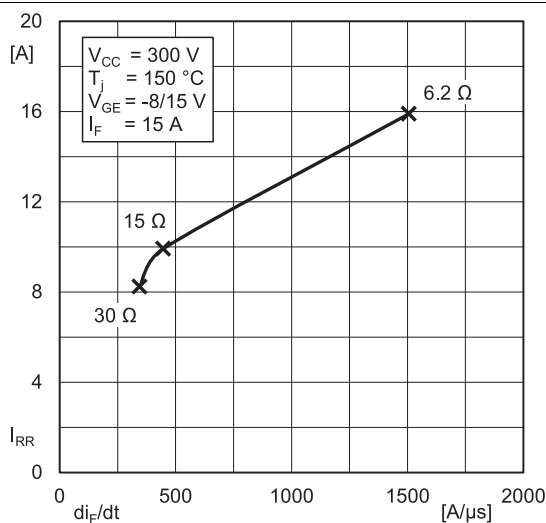


Fig. 11: Typ. Diode peak reverse recovery current

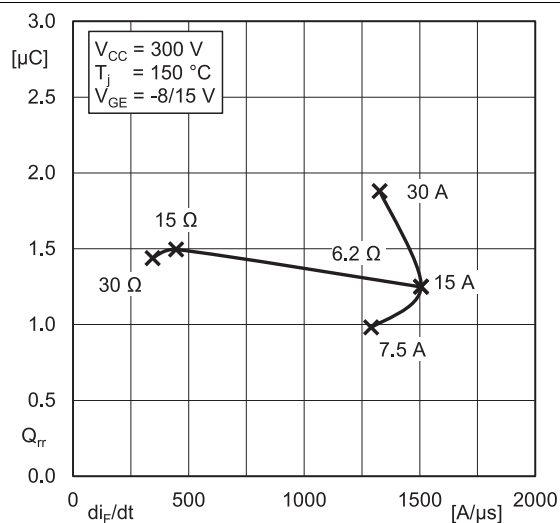
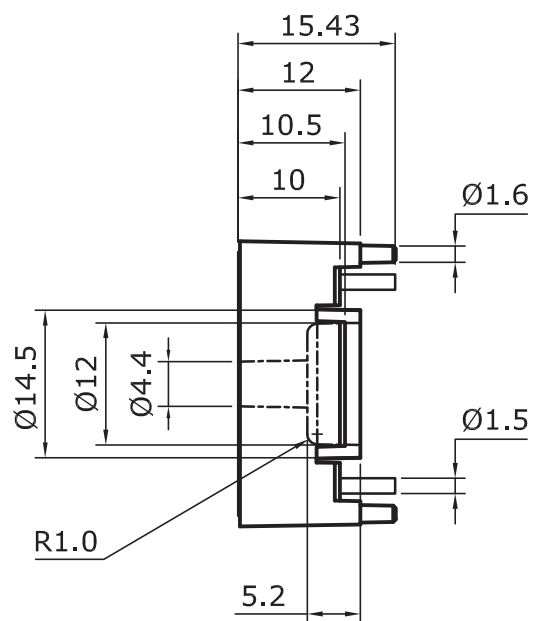
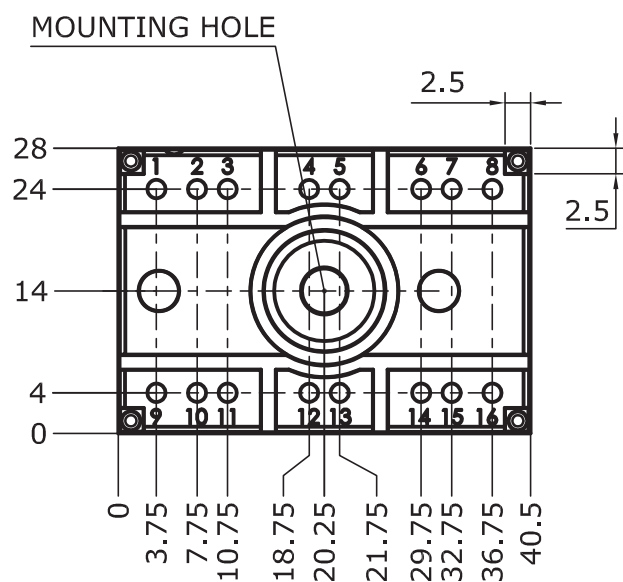
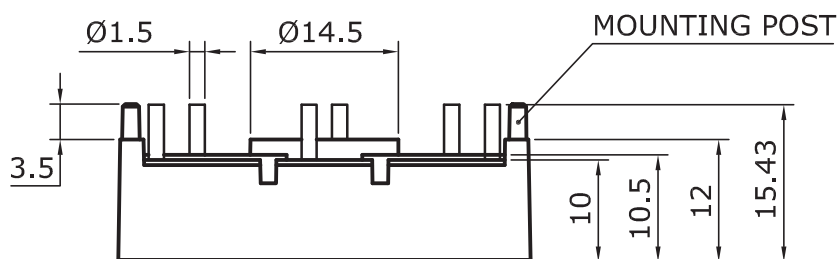


Fig. 12: Typ. Diode reverse recovery charge

Dimensions: mm

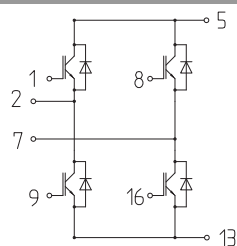
Tolerance system: ISO 2768-m



Suggested hole diameter for solder pins in the circuit board:

- 2.0 mm

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This is an electrostatic discharge sensitive device (ESDS) due to international standard IEC 61340.

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